

Abstracts

Design, Fabrication and Evaluation of Tunnel Transit-Time Diodes for V-Band and W-Band Power Generation

C. Kidner, H. Eisele, J. East and G.I. Haddad. "Design, Fabrication and Evaluation of Tunnel Transit-Time Diodes for V-Band and W-Band Power Generation." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 1089-1092.

Tunnel injection Transit-Time (TUNNETT) diodes are very promising for medium power, low noise applications up to THz frequencies. We have successfully designed and tested GaAs p⁺/n⁺/n⁺/n⁺ single-drift TUNNETT diodes for V-band and W-band operation. We have measured 26 mW at 58.0 GHz and 33 mW at 93.5 GHz with good spectra.

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